

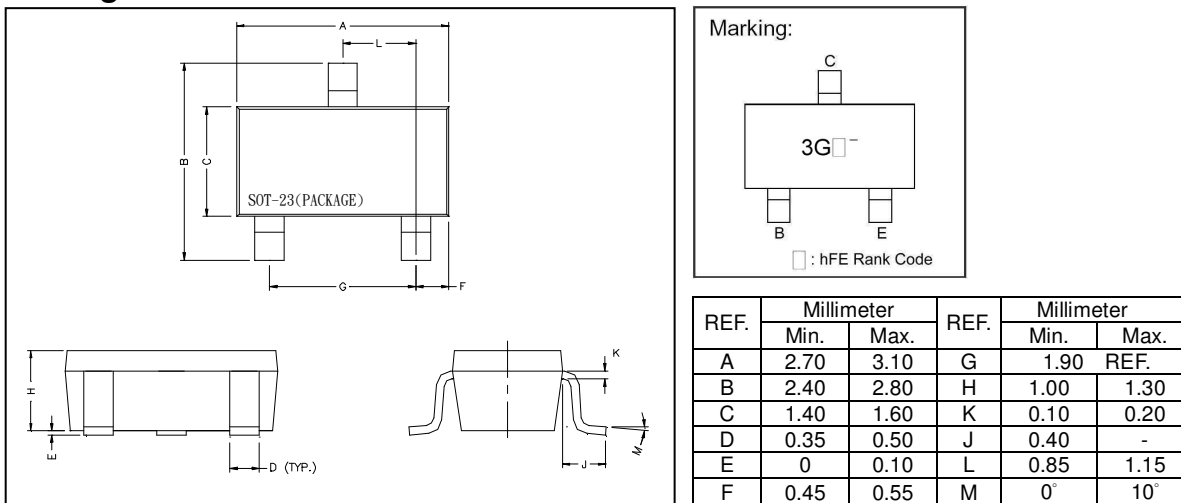
## GMBT9015

### PNP EPITAXIAL PLANAR TRANSISTOR

#### Description

The GMBT9015 is designed for use in pre-amplifier of low level and low noise.

#### Package Dimensions



#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-50	V
Collector to Emitter Voltage	VCEO	-45	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-100	mA
Total Power Dissipation	PD	225	mW

#### Characteristics at Ta = 25°C

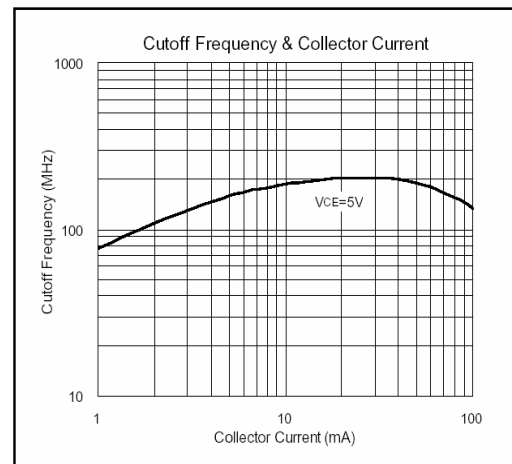
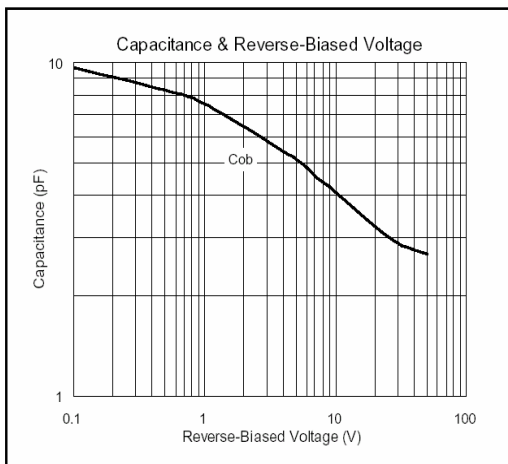
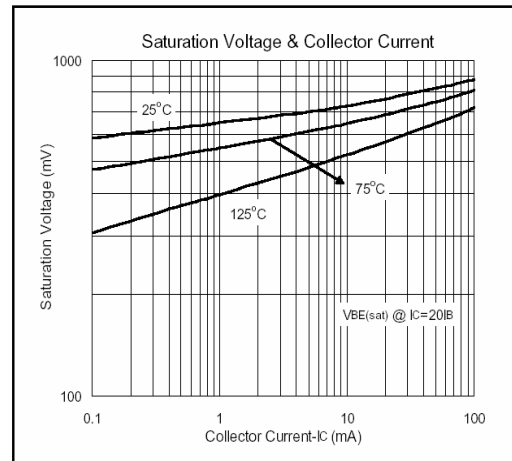
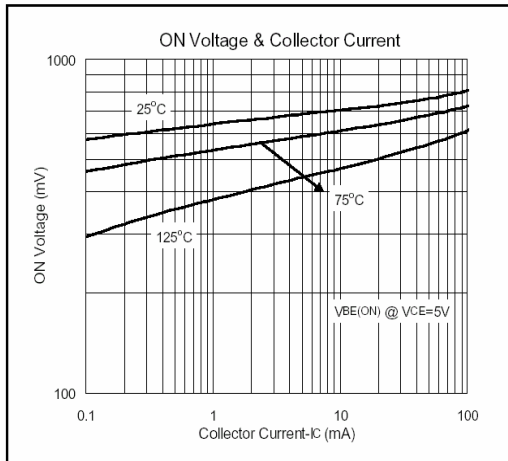
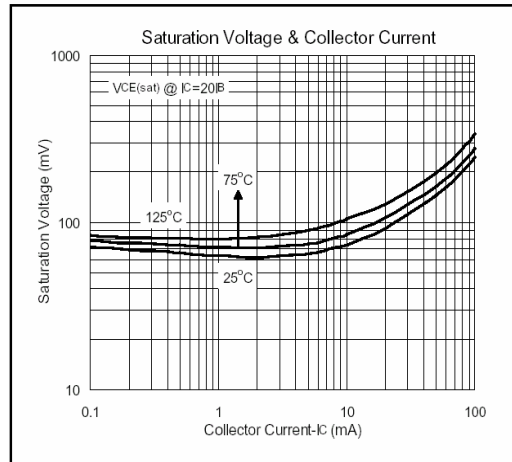
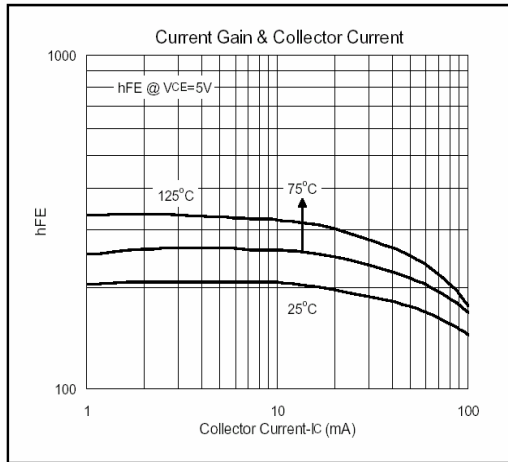
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-50	-	-	V	IC=-100uA, IE=0
BVCEO	-45	-	-	V	IC=-1mA, IB=0
BVEBO	-5	-	-	V	IE=-100uA, IC=0
ICBO	-	-	-50	nA	VCB=-50V, IE=0
IEBO	-	-	-50	nA	VEB=-5V, IC=0
*VCE(sat)1	-	-0.2	-0.7	V	IC=-100mA, IB=-5mA
*VCE(sat)2	-	-0.82	-1	V	IC=-100mA, IB=-5mA
VBE(on)	-0.6	-0.65	-0.75	V	VCE=-5V, IC=-2mA
*hFE	100	200	600		VCE=-5V, IC=-1mA
fT	100	190	-	MHz	VCE=-5V, IC=-10mA
Cob	-	4.5	7	pF	VCB=-10V, f=1MHz, IE=0

\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

#### Classification Of hFE

Rank	B	C
Range	100-300	200-600

## Characteristics Curve



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